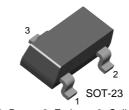




### **FMMT549 PNP Low Saturation Transistor**

### **Features**

- · This device is designed with high current gain and low saturation voltage with collector currents up to 2A continous.
- · Sourced from process PB.



1. Base 2. Emitter 3. Collector

### Absolute Maximum Ratings \* Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>CBO</sub>	Collector-Base Voltage	-35	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current - Continuous - Peak Pulse Current	-1 -2	A A
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

### Thermal Characteristics \*

Symbol	Parameter	Value	Unit
$P_{D}$	Total Device Dissipation, by R <sub>θJA</sub> Derate above 25°C	500 4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

<sup>\*</sup> Device mounted on FR-4 PCB 4.5" X 5", mounting pad 0.02 in<sup>2</sup> of 2 oz copper.

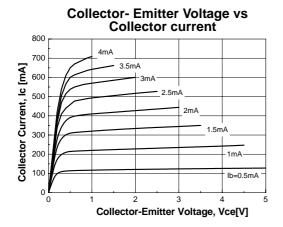
These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

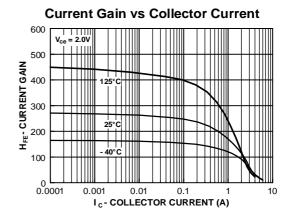
### Electrical Characteristics\* T<sub>C</sub> = 25°C unless otherwise noted

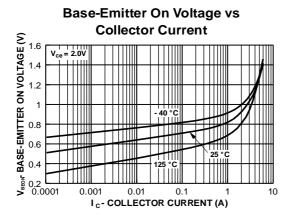
Symbol	Parameter	Conditions	Min.	Max.	Units
Off Characte	ristics			1	•
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = -10 \text{mA}, I_B = 0$	-30		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-35		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = -30V, I_{E} = 0$ $V_{CB} = -30V, I_{E} = 0, T_{a} = 100^{\circ}C$		-100 -10	nA μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4.0V, I <sub>C</sub> =0		-100	nA
On Characte	ristics *				
h <sub>FE</sub>	DC Current Gain	$\begin{aligned} & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-50mA} \\ & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-500mA} \\ & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-1A} \\ & V_{\text{CE}} = \text{-2.0V}, \ I_{\text{C}} = \text{-2A} \end{aligned}$	70 100 80 40	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA		-500 -750	mV mV
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = -1A, I_B = -100mA$		-1.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2.0V		-1.0	V
Small Signal	Characterics				
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -5V, f = 100MHz	100		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$		25	pF

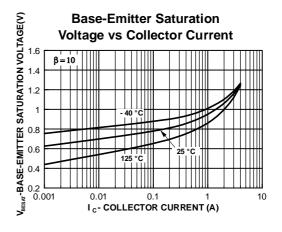
<sup>\*</sup> DC Item are tested by Pulse Test: Pulse Width≤300us, Duty Cycle≤2%

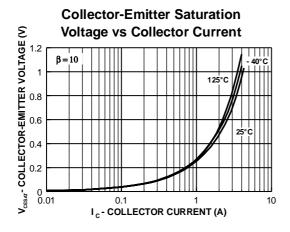
### **Typical Characteristics**

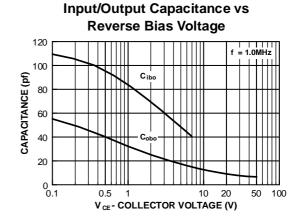






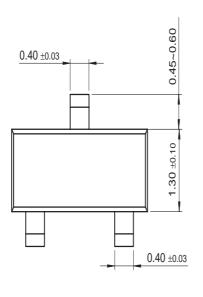


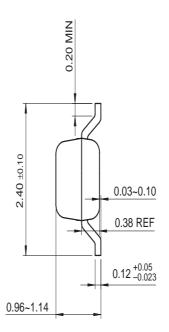


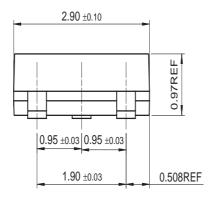


# **Package Dimensions**

# **SOT-23**







Dimensions in Millimeters

UltraFET® UniFET™ VCX™ Wire™

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Across the board. Around the world.™		μSerDes™	TruTranslation™
The Power Franchise®		ScalarPump™	UHC™

Programmable Active Droop™

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### **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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